TOSHIBA Field Effect Transistor Silicon N-Channel MOS Type (U-MOSVI-H)

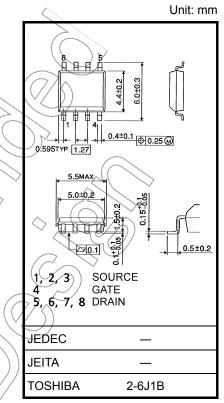
# ТРС8040-Н

High Efficiency DC-DC Converter Applications Notebook PC Applications Portable Equipment Applications

- Small footprint due to a small and thin package
- High-speed switching
- Small gate charge: QSW = 5.1 nC (typ.)
- Low drain-source ON-resistance:  $RDS(ON) = 6.4 \text{ m}\Omega$  (typ.)
- High forward transfer admittance:  $|Y_{fs}| = 48 \text{ S} (typ.)$
- Low leakage current:  $I_{DSS} = 10 \ \mu A \ (max) \ (V_{DS} = 30 \ V)$
- Enhancement mode:  $V_{th} = 1.3$  to 2.3 V ( $V_{DS} = 10$  V,  $I_D = 0.2$  mÅ)

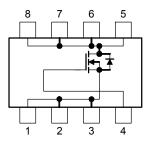
#### Absolute Maximum Ratings (Ta = 25°C)

			$\langle \bigcirc \rangle$	$\sim$
Characteristic		Symbol	Rating	Unit
Drain-source voltage		V <sub>DSS</sub>	30	V
Drain-gate voltage ( $R_{GS} = 20 \text{ k}\Omega$ )		V <sub>DGR (</sub>	30	V
Gate-source voltage		V <sub>GSS</sub>	±20	< <v td=""  <=""></v>
Drain current	DC (Note 1)	ID	13	A
	Pulsed (Note 1)		52	
Drain power dissipation $(t = 10 s)$			1.9 ~	w
(Note 2a)				$\geq$
Drain power dissipation (t = 10 s) (Note 2b)		7 PD	1.0	Ŵ
Single pulse avalanche energy (Note 3)		EAS	110	mJ
Avalanche current		IAR	13	A
Repetitive avalarche energy		Ear	2.0	mJ
Channel temperature		Tch	150	°C
Storage temperature range		T <sub>stg</sub>	–55 to 150	°C



Weight: 0.085 g (typ.)

#### **Circuit Configuration**



Note: For Notes 1 to 4, refer to the next page.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating" Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc.).

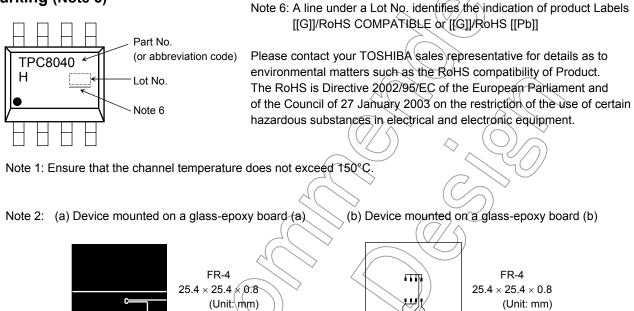
This transistor is an electrostatic-sensitive device. Handle with care.

## TOSHIBA

### **Thermal Characteristics**

Characteristic	Symbol	Max	Unit
Thermal resistance, channel to ambient $(t = 10 \ s)$ (Note 2a)	R <sub>th (ch-a)</sub>	65.8	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2b)	R <sub>th (ch-a)</sub>	125	°C/W

#### Marking (Note 5)



(b)

Note 3:  $V_{DD} = 24 \text{ V}, \text{ T}_{ch} = 25^{\circ} \text{C}$  (initial), L = 500 µH, R<sub>G</sub> = 25  $\Omega$ , L<sub>AR</sub> = 13 A

Note 4: Repetitive rating: pulse width limited by maximum channel temperature

- Note 5: on lower left of the marking indicates Pin 1.
  - \* Weekly code: (Three digits)

(a)

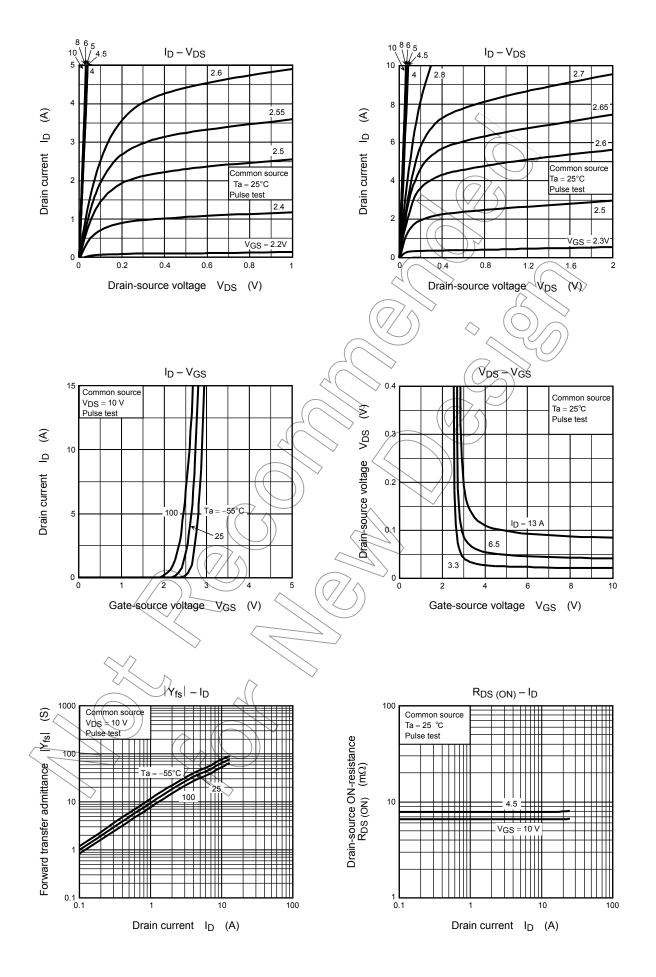


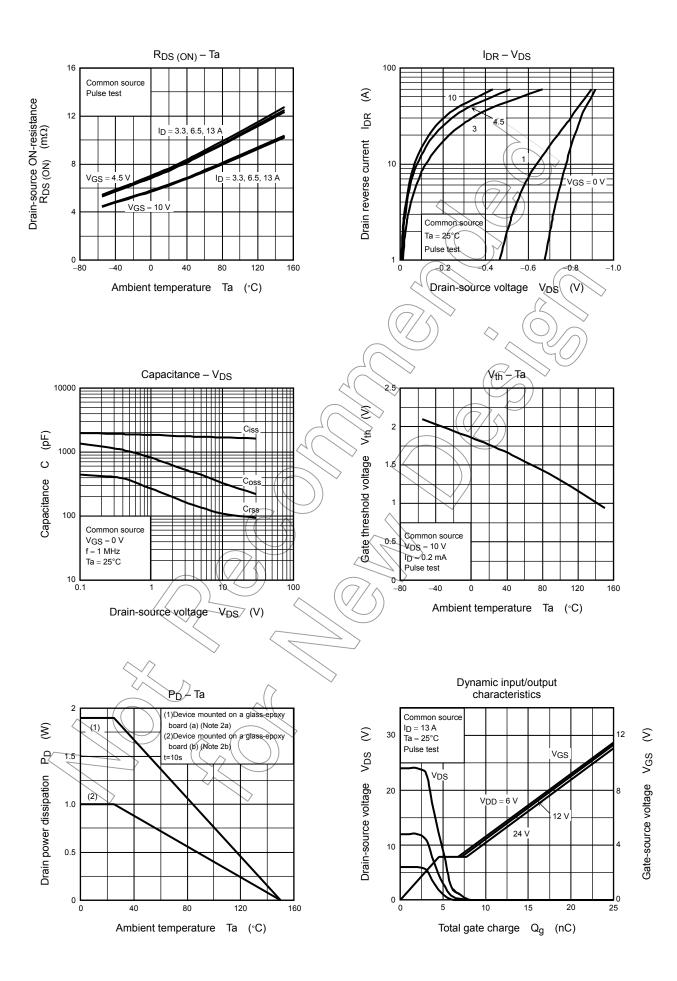
**Electrical Characteristics (Ta = 25°C)** 

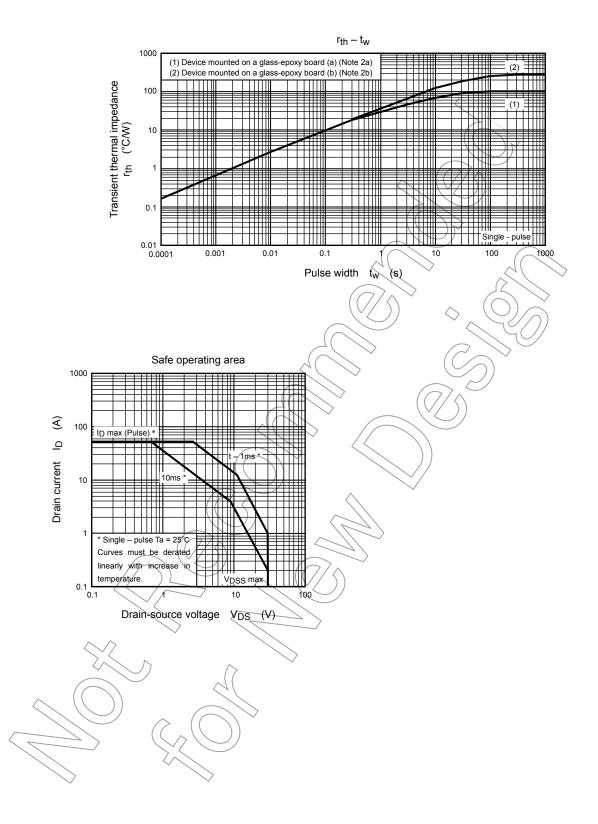
Ch	aracteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cui	rrent	I <sub>GSS</sub>	$V_{GS}=\pm 20~V,~V_{DS}=0~V$		_	±100	nA
Drain cutoff curre	ent	I <sub>DSS</sub>	$V_{DS} = 30 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$			10	μA
Drain-source breakdown voltage		V (BR) DSS	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	30	_	_	v
		V (BR) DSX	$I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$	15		_	v
Gate threshold v	oltage	V <sub>th</sub>	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 0.2 \text{ mA}$	1.3	-7(	2.3	V
Drain-source ON-resistance		R <sub>DS (ON)</sub>	$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 6.5 \text{ A}$	$\sum$	7.7	11.1	mΩ
			$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 6.5 \text{ A}$	$\bigcirc$	6.4	9.7	1115.2
Forward transfer	admittance	Y <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 7 A	24	48	_	S
Input capacitance	9	C <sub>iss</sub>			1700	2200	
Reverse transfer capacitance		C <sub>rss</sub>	$V_{DS} = 10 V, V_{GS} = 0 V, f = 1 MHz$		110	170	pF
Output capacitance		C <sub>oss</sub>			<330	$\searrow$	
Gate resistance		rg	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 5 \text{ MHz}$	-6	2.3	> 3.5	Ω
Switching time	Rise time	tr	$10\sqrt{N}$ $lp = 6.5 A$	<	5.5	) _	
	Turn-on time	t <sub>on</sub>	$V_{GS}$ $0$ $V_{OUT}$ $I_D = 6.5 \text{ A}$ $V_{GS}$ $V_{OUT}$ $V_{OUT}$ $V_{OUT}$ $V_{OUT}$ $V_{OUT}$	20	15	_	
	Fall time	t <sub>f</sub>			8.6	_	ns
	Turn-off time	toff	$V_{DD} \approx 15$ V Duty $\leq 1\%$ , t <sub>w</sub> $\neq 10$ µs	_	39	_	
Total gate charge (gate-source plus gate-drain)		Qg	$V_{DD} \approx 24 \text{ V}, \text{ V}_{GS} = 10 \text{ V}, \text{ I}_{D} = 13 \text{ A}$		24	_	
			$V_{DD} \approx 24 \text{ V}, V_{GS} = 5 \text{ V}, I_D = 13 \text{ A}$		12	_	
Gate-source cha	rge 1	Qĝs1	$\wedge$		4.6	_	nC
Gate-drain ("mille	er") charge	Qgd	$V_{DD} \approx 24 V, V_{GS} = 10 V, I_{D} = 13 A$		3.2	_	
Gate switch char	ge	QSW		—	5.1	_	

## Source-Drain Ratings and Characteristics (Ta $\neq$ 25°C)

Characteristics	Symbol Test Condition	Min	Тур.	Max	Unit
Drain reverse current Pulse (Note 1)	I <sub>DRP</sub> —	_	_	52	А
Forward voltage (diøde)	$V_{\text{DSF}}$ $I_{\text{DR}} = 13 \text{ A}, V_{\text{GS}} = 0 \text{ V}$			-1.2	V







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